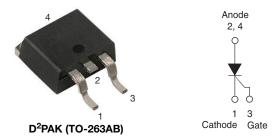
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Thyristor Surface Mount, Phase Control SCR, 8 A



8 A

800 V

1.2 V

15 mA

-40 to +125 °C

D²PAK (TO-263AB)

Single SCR

PRIMARY CHARACTERISTICS

I_{T(AV)}

V_{DRM}/V_{RRM}

V_{TM}

ТJ

Package

Circuit configuration

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FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-12TTS08SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
Capacitive input filter $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, common heatsink of 1 °C/W	13.5	17	А				

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I _{T(AV)}	Sinusoidal waveform	8	Α				
I _{T(RMS)}		12.5	A				
V _{RRM} /V _{DRM}		800	V				
I _{TSM}		110	A				
V _T	8 A, T _J = 25 °C	1.2	V				
dV/dt		150	V/µs				
dl/dt		100	A/µs				
TJ	Range	-40 to +125	°C				

VOLTAGE RATINGS								
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} / I _{DRM} AT 125 °C mA					
VS-12TTS08SLHM3	800	800	5.0					

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COMPLIANT HALOGEN

VS-12TTS08SLHM3



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 108 °C, 180° conduction, half sine wave	8				
Maximum RMS on-state current	I _{T(RMS)}	$T_{\rm C} = 100$ C, 100 conduction, that sine wave	12.5				
Maximum peak one-cycle	L	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	95	A			
non-repetitive surge current	ITSM	10 ms sine pulse, no voltage reapplied, T_J = 125 °C	110				
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s			
Maximum - tior fusing	1-1	10 ms sine pulse, no voltage reapplied, T_J = 125 °C	64	A-S			
Maximum I ² √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, T_{J} = 125 $^{\circ}\text{C}$	640	A²√s			
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V			
On-state slope resistance	r _t	T_I = 125 °C		mΩ			
Threshold voltage	V _{T(TO)}	1) = 125 0	0.87	V			
Maximum reverse and direct leakage current	1/1	$T_J = 25 \text{ °C}$	0.05				
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_J = 125 \text{ °C}$ $V_R = \text{rated } V_{RRM} / V_{DRM}$	5.0				
Typical holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	30	mA			
Typical latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C	50				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = open$	150	V/µs			
Maximum rate of rise of turned-on current	dl/dt		100	A/µs			

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	vv
Maximum peak positive gate current	+I _{GM}		1.5	А
Maximum peak negative gate voltage	-V _{GM}		10	V
		Anode supply = 6 V, resistive load, T_J = - 65 °C	20	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	15	mA
		Anode supply = 6 V, resistive load, T_J = 125 °C	10	
		Anode supply = 6 V, resistive load, T_J = -65 °C	1.2	
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	1	V
		Anode supply = 6 V, resistive load, T_J = 125 °C	0.7	V
Maximum DC gate voltage not to trigger	V _{GD}	$T_{\rm J} = 125 \ ^{\circ}{\rm C}, \ V_{\rm DRM} = rated \ value \qquad \qquad$		
Maximum DC gate current not to trigger	I _{GD}			mA

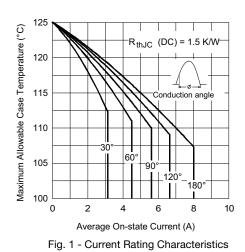
SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8	
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	3	μs
Typical turn-off time	tq	1J = 123 C	100	

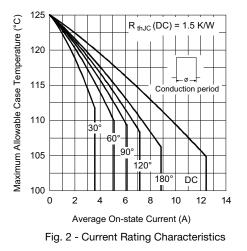
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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.5			
Maximum thermal resistance, junction to ambient	R _{thJA}		62	°C/W		
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, and greased	0.5			
Approximate weight			2	g		
			0.07	oz.		
Marking device		Case style D ² PAK (TO-263AB)	12TTS	608SH		





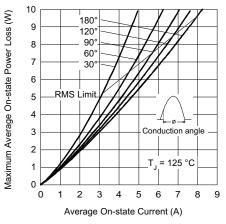


Fig. 3 - On-State Power Loss Characteristics

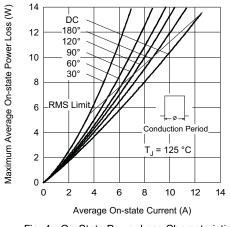
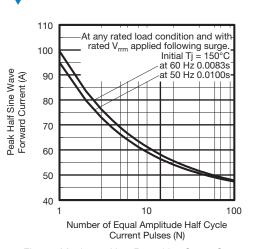


Fig. 4 - On-State Power Loss Characteristics

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Fig. 5 - Maximum Non-Repetitive Surge Current

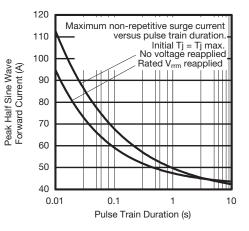


Fig. 6 - Maximum Non-Repetitive Surge Current

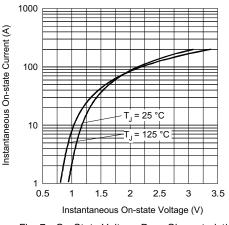


Fig. 7 - On-State Voltage Drop Characteristics

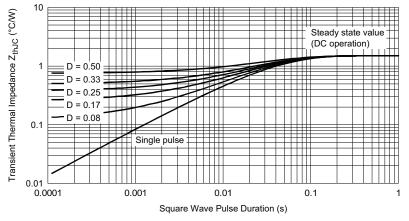


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

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ISHA

Device code	VS-	12	т	т	s	08	S	L	н	М3
		2	3	4	5	6	7	8	9	10
	 Vishay Semiconductors product Current rating (12.5 A) Circuit configuration: T = single thyristor Package: T = D²PAK (TO-263AB) Type of silicon: 									
	6 - 7 - 8 - 9 - 10 -	Voli S = L = H =	tage rati surface tape an AEC-Q rironmer	101 qua ntal digit	= 800 V) able eft orien alified ::	ted), foi				ontact fa ad (Pb)-f

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-12TTS08SLHM3	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96317				

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NULES
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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